

In The Claims

Please amend the claims as follows:

1. (Currently Amended) A multi-finger type ESD protection device comprising:

a semiconductor substrate;

a plurality of first active regions formed on the semiconductor substrate;

a plurality of gates formed in each of the first active regions;

a single second active region of a predetermined conductive type formed additionally between the first active regions, wherein the second active region includes an n+ junction connected to Vcc reference voltage or a p+ junction connected to ground Vss, and is without a gate, a source and a drain; ~~and~~

a third active region surrounding the first and second active regions and being of conductivity type different from that of the first active regions; and

a plurality of drain regions formed in each of the first active regions,

wherein the drain regions include a pair of drain regions formed at n+ junctions of both end portions of each of the first active regions.

Claims 2-6. (Canceled)

7. (Previously Presented) The device of claim 1, further comprising:

a plurality of source regions each formed between a pair of gates in each of the first active regions.

8. (Previously Presented) The device of claim 1, wherein the first and second active regions and the gates extend substantially parallel to each other.

9. (Original) The device of claim 8, wherein the first and second active regions and the gates have a substantially same shape.

10. (Canceled)

11. (Currently Amended) A multi-finger type ESD protection device comprising:

a semiconductor substrate;

a plurality of first active regions formed separately on the semiconductor substrate;

a plurality of gates formed in each of the first active regions; ~~and~~

a single predetermined conductive type second active region formed between two of the first active regions, wherein the predetermined conductive type second active region includes an n+ junction connected to Vcc reference voltage, and is without a gate, a source and a drain; and

drain regions formed at n+ junctions of both end portions of the first active regions.

Claims 12-14. (Canceled)

15. (Original) The device of claim 11, further comprising:
source regions each formed between two gates in each of the first active regions.

16. (Original) The device of claim 11, wherein the first and second active regions and the gates extend substantially parallel to each other and have a substantially same shape.

17. (Previously Presented) The device of claim 11, further comprising:
a third active region surrounding completely the first and second active regions.

18. (Currently Amended) A multi-finger type ESD protection device comprising:
a semiconductor substrate;
a plurality of first active regions formed separately on the semiconductor substrate;

a plurality of gates formed in each of the first active regions; ~~and~~
a single second active region of a predetermined conductive type, formed
between the first active regions, wherein the predetermined conductive type
second active region includes a p⁺ junction connected to ground V_{ss}, and is
without a gate, a source and a drain; and
drain regions formed at n⁺ junctions of both end portions of the first
active regions.

Claims 19-20. (Canceled)

21. (Previously Presented) The device of claim 1, wherein the third active
region surrounds completely the first and second active regions.

22. (Previously Presented) The device of claim 21, wherein the third
active region has a ring configuration.

23. (Previously Presented) The device of claim 1, wherein the first active
region is of p conductive type.

24. (Cancelled)

25. (Previously Presented) The device of claim 18, further comprising:

source regions each formed between the gates in each of the first active regions.

26. (Previously Presented) The device of claim 18, wherein the first and second active regions and the gates extend substantially parallel to each other and have a substantially same shape.

27. (Previously Presented) The device of claim 18, wherein spaces are provided between the first and second active regions.

28. (Previously Presented) A multi-finger type ESD protection device comprising:

- a semiconductor substrate;

- a plurality of first active regions formed on the semiconductor substrate;

- a plurality of gates formed in each of the first active regions;

- at least one second active region of a predetermined conductive type formed additionally between the first active regions, wherein the second active region includes an n⁺ junction connected to V_{cc} reference voltage or a p⁺ junction connected to ground V_{ss};

- a third active region surrounding the first and second active regions and being of conductivity type different from that of the first active regions; and

- a plurality of drain regions formed in each of the first active regions,

wherein the drain regions include a pair of drain regions formed at n+ junctions of both end portions of each of the first active regions.

29. (Previously Presented) A multi-finger type ESD protection device comprising:

a semiconductor substrate;

a plurality of first active regions formed separately on the semiconductor substrate;

a plurality of gates formed in each of the first active regions;

at least one predetermined conductive type second active region formed between two of the first active regions, wherein the predetermined conductive type second active region is an n+ junction connected to Vcc reference voltage; and

drain regions formed at n+ junctions of both end portions of the first active regions.

30. (Previously Presented) A multi-finger type ESD protection device comprising:

a semiconductor substrate;

a plurality of first active regions formed separately on the semiconductor substrate;

a plurality of gates formed in each of the first active regions;

at least one second active region of a predetermined conductive type, formed between the first active regions, wherein the predetermined conductive type second active region includes a p⁺ junction connected to ground V_{ss};

a third active region surrounding the first and second active regions and being of conductivity type different from that of the first active regions; and

drain regions formed at n⁺ junctions of both end portions of the first active regions.

31. (Cancelled)

32. (Previously Presented) The device of claim 18, further comprising:

a third active region surrounding completely the first and second active regions.